



File

Attorney's Docket No. 42P15685

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Scott A. Hareland, et al.

Application No.: 10/607,769

Filed: June 27, 2003

For: Nonplanar Semiconductor Device with
Partially or Fully Wrapped Around Gate
Electrode and Methods of Fabrication

Examiner: Unassigned

Art Unit: 2812

Mail Stop Amendment
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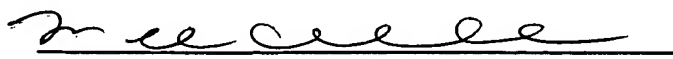
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If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: February 15, 2007


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INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	10/607,769
Filing Date	June 27, 2003
First Named Inventor:	Scott A. Hareland
Art Unit	2812
Examiner Name	Such, Matthew W.
Attorney Docket No.:	42P15685

Sheet 1 of 4

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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				Art Unit	2812
				Examiner Name	Such, Matthew W.
Sheet	3	of	4	Attorney Docket Number	42P15685
NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
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